

Silicon PNP Power Transistors

BDX66C

DESCRIPTION

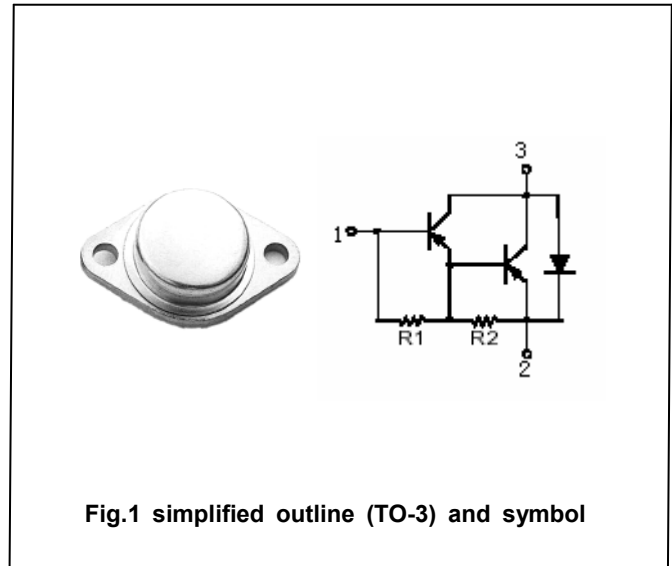
- With TO-3 package
- DARLINGTON
- High current

APPLICATIONS

- Designed for power amplification and switching applications.

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-120	V
V_{CEO}	Collector-emitter voltage	Open base	-120	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-16	A
I_{CM}	Collector current(peak)		-20	A
I_B	Base current		-0.25	A
P_T	Total power dissipation	$T_C=25^\circ\text{C}$	150	W
T_j	Junction temperature		-55~200	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal resistance from junction to case	1.17	$^\circ\text{C}/\text{W}$

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CHARACTERISTICS

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 $T_j = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-emitter sustaining voltage	$I_C = -0.1\text{A}$; $I_B = 0$; $L = 25\text{mH}$	-120			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -10\text{A}$; $I_B = -40\text{mA}$			-2	V
I_{CBO}	Collector cut-off current	$V_{CB} = -70\text{V}$; $I_E = 0$ $T_C = 150^\circ\text{C}$			-1 -5	mA
I_{CEO}	Collector cut-off current	$V_{CE} = -60\text{V}$; $I_B = 0$			-3	mA
I_{EBO}	Emitter cut-off current	$V_{EB} = -5\text{V}$; $I_C = 0$			-5	mA

Switching times

t_{on}	Turn-on time	$I_C = -10\text{A}$; $I_{B1} = -I_{B2} = 0.04\text{A}$ $V_{CC} = 12\text{V}$;		1.0		μs
t_{off}	Turn-off time			3.5		μs

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PACKAGE OUTLINE

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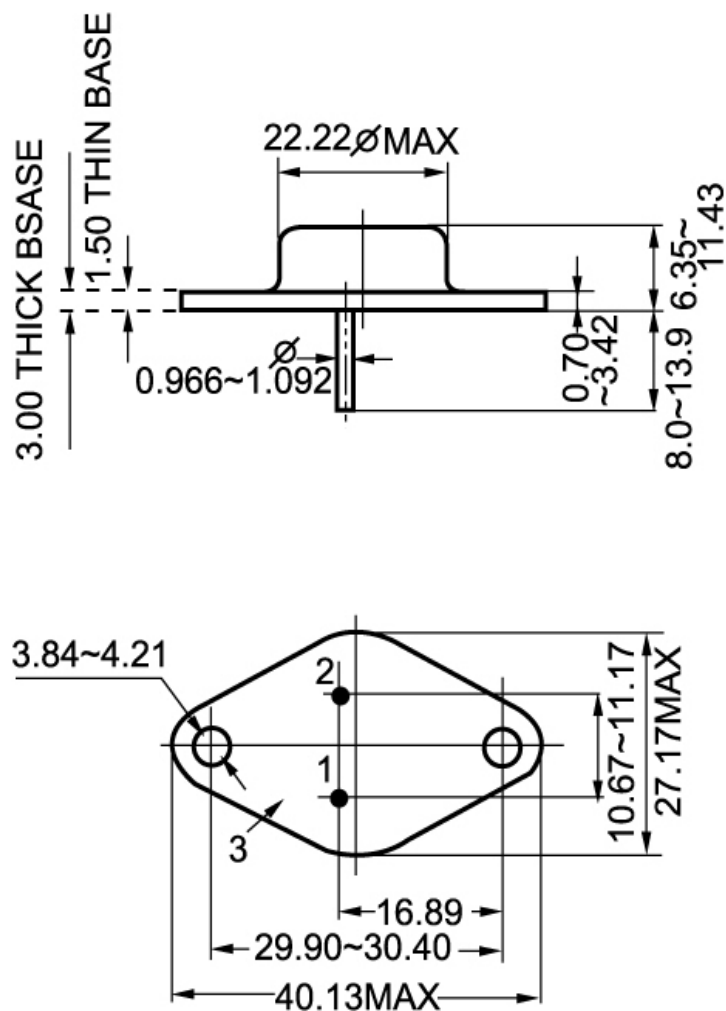


Fig.2 Outline dimensions